

3-Cell, High-Efficiency, Step-Up DC/DC Converter

FEATURES

- 4V to 24V Input Voltage Operation.
- Adjustable Output Voltage.
- Low Quiescent Current at 100 μ A.
- Pulse-Skipping and Pulse-Frequency Modulation Maintain High Efficiency (max. 95%).
- 90KHz to 250KHz Oscillator Frequency.
- Power-Saving Shutdown Mode (8 μ A Typical).
- Push-Pull Driver Output.

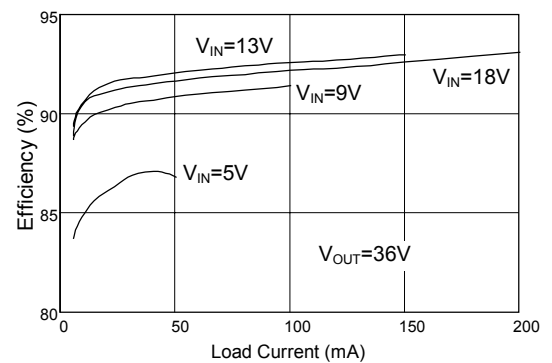
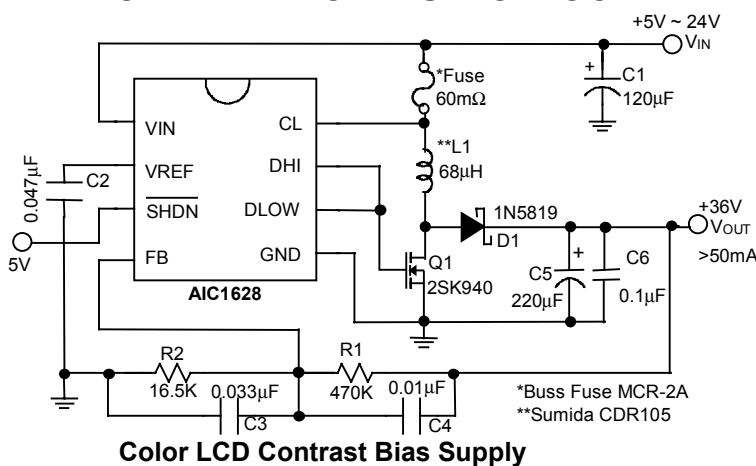
APPLICATIONS

- Flash Memory Programming Power Supply.
- Positive LCD Contrast Bias for Notebook & Palmtop Computers.
- Step-Up DC/DC Converter Module.
- Telecom Power Supply.

DESCRIPTION

The AIC1628 is a high performance step-up DC/DC converter, designed to drive an external power switch to generate programmable positive voltages. In the particularly suitable LCD contrast bias and flash memory programming power supply applications, typical full-load efficiencies are 85% to 95%. 4V to 24V input operation range allows the AIC1628 to be powered directly by the battery pack in the most battery-operated applications for greater efficiency. Output voltage can be scaled to 40V or greater by two external resistors. A Pulse-Frequency Modulation scheme is employed to maintain high efficiency conversion under wide input voltage range. Quiescent current is about 100 μ A and can be reduced to 8 μ A in shutdown mode. Switching frequency being around 90KHz to 250KHz range, small size switching components are ideal for battery powered portable equipments, like notebook and palmtop computers.

TYPICAL APPLICATION CIRCUIT



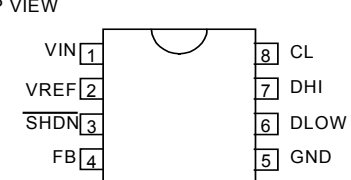
Efficiency vs. Output Current

ORDERING INFORMATION

AIC1628 XX

PACKAGE TYPE
 N: PLASTIC DIP
 S: SMALL OUTLINE

TEMPERATURE RANGE
 C=0°C~+70°C

| ORDER NUMBER | PIN CONFIGURATION |
|----------------------------|---|
| AIC1628CN (PLASTIC DIP) | TOP VIEW  |
| AIC1628CS (PLASTIC SO) | |

ABSOLUTE MAXIMUM RATINGS

| | |
|--|--------------|
| V _{IN} Supply Voltage (V _{IN} Pin) | 24V |
| SHDN Pin Voltage | 15V |
| Operating Temperature Range | 0°C~70°C |
| Storage Temperature Range | -65°C~ 150°C |

TEST CIRCUIT

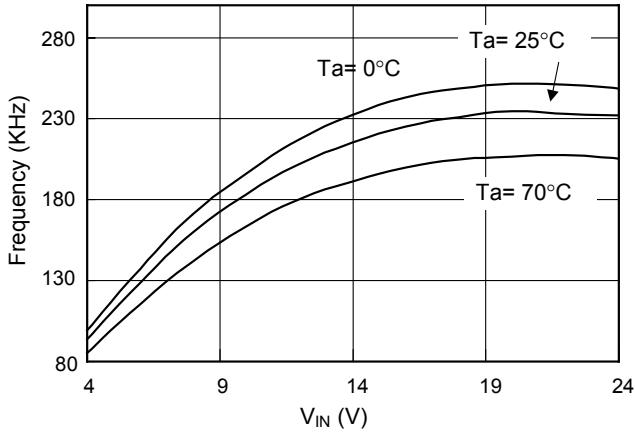
Refer to Typical Application Circuit

ELECTRICAL CHARACTERISTICS (V_{IN}= 13V, T_a=25°C, unless otherwise specified.)

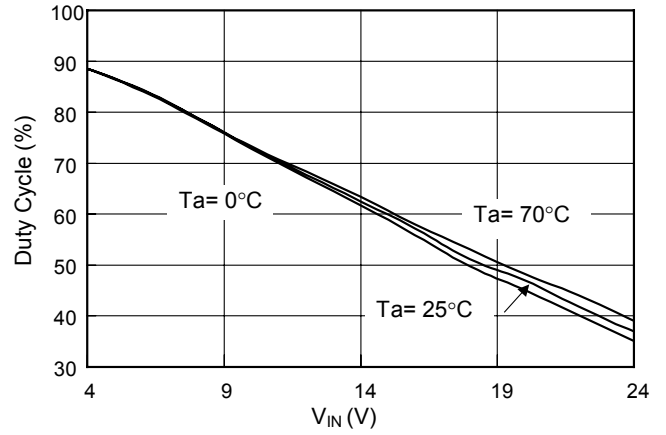
| PARAMETERS | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------------------|-----------------------------------|------|------|------|------|
| Input Voltage | | 4 | | 24 | V |
| Quiescent Current | V _{FB} = 1.5V | | 100 | 200 | μA |
| Shutdown Mode Current | V _{SHDN} = 0V | | 8 | 20 | μA |
| V _{REF} Voltage | I _{SOURCE} = 250μA | 1.16 | 1.22 | 1.28 | V |
| V _{REF} Source Current | | 250 | | | μA |
| DLOW "ON Resistance" | | | 15 | | Ω |
| DHI "ON Resistance" | | | 10 | | Ω |
| CL Threshold | V _{IN} - V _{CL} | 45 | 60 | 75 | mV |
| Shutdown Threshold | | 0.8 | 1.5 | 2.4 | V |
| Shutdown Input Leakage Current | V _{SHDN} < 15V | | | 1 | μA |

TYPICAL PERFORMANCE CHARACTERISTICS

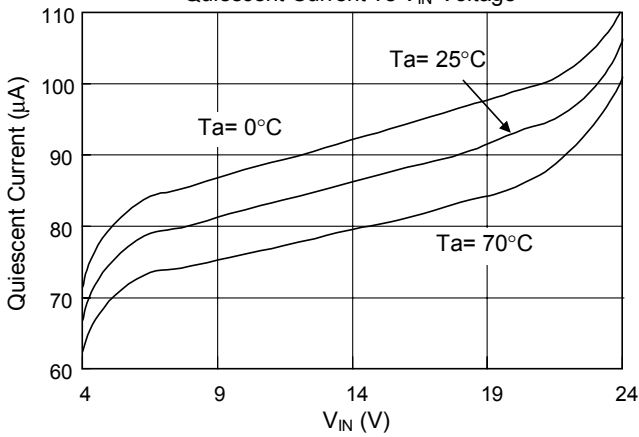
Frequency vs V_{IN} Voltage



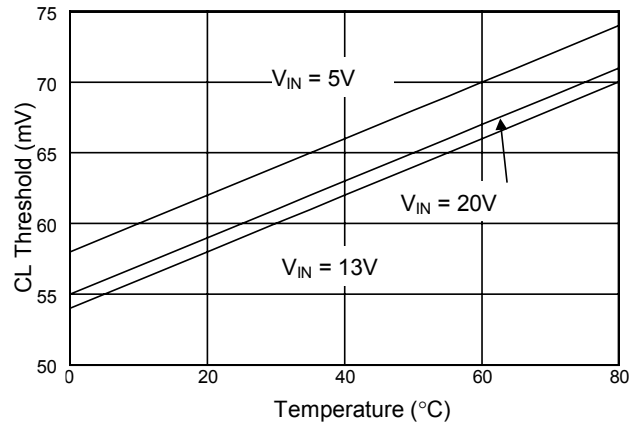
Duty Cycle vs V_{IN} Voltage



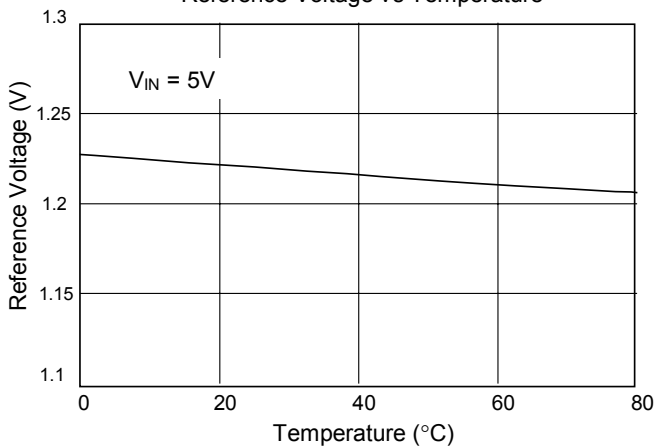
Quiescent Current vs V_{IN} Voltage

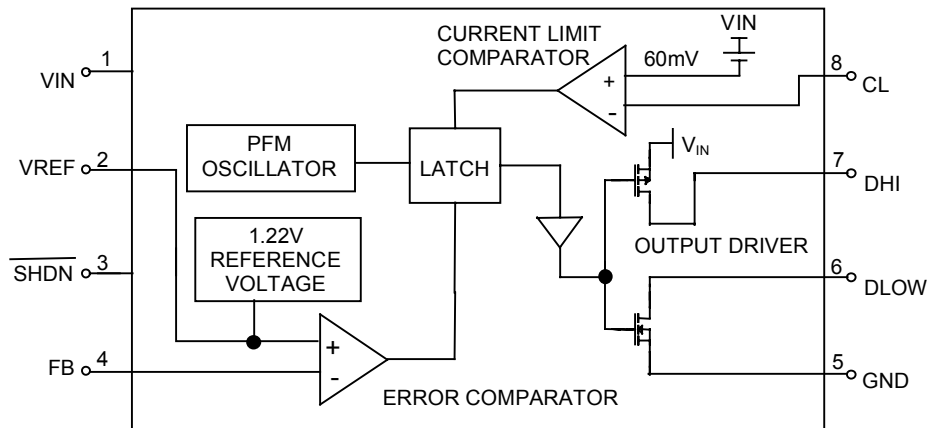


Current Limit Threshold vs Temperature



Reference Voltage vs Temperature



■ BLOCK DIAGRAM

■ PIN DESCRIPTIONS

- PIN 1: VIN - 4V to 24V input supply voltage.
- PIN 2: VREF - 1.22V reference output. Bypass with a 0.047 μ F capacitor to GND. Sourcing capability is guaranteed to be greater than 250 μ A.
- PIN 3: $\overline{\text{SHDN}}$ - Logical input to shutdown the chip.
>1.5V = normal operation,
GND = Shutdown,
Can not be floating or forced greater than 15V. In shutdown mode DLOW and DHI pins are at low level.
- PIN 4: FB- Feedback signal input to sense VREF. Connecting a resistance R1 to V_{OUT} and a resistance R2 to GND yields the output voltage:
 $V_{\text{OUT}} = (R1+R2)/R2 \times V_{\text{REF}}$
(Refer to typical application circuit)

- PIN 5: GND - Power ground.
- PIN 6: DLOW -Driver sinking output. Connected to gate of the external N-channel MOSFET or base of the NPN bipolar transistor.
- PIN 7: DHI - Driver sourcing output. Connected to DLOW when using an external N-channel MOSFET. When using an external NPN bipolar transistor, connect a base resistance RB from this pin to DLOW. RB value depends on V_{IN}, inductor and NPN current gain.
- PIN 8: CL - Current-limit input. Threshold voltage is 60mV from V_{IN}. This pin clamps the switch peak current to prevent over-current damage to the external switch, under abnormal conditions.

APPLICATION EXAMPLES

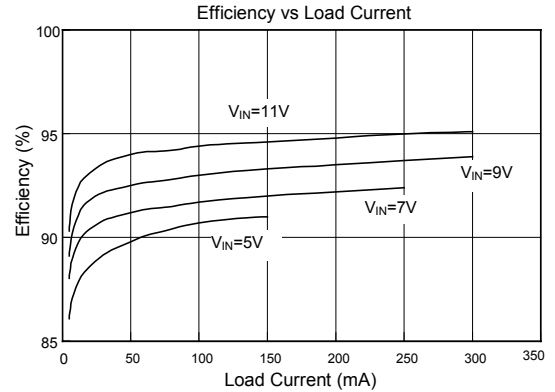
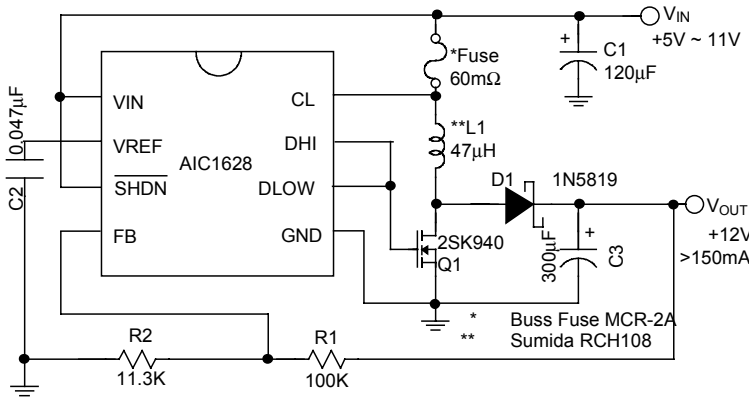


Fig. 1 Flash memory programming supply

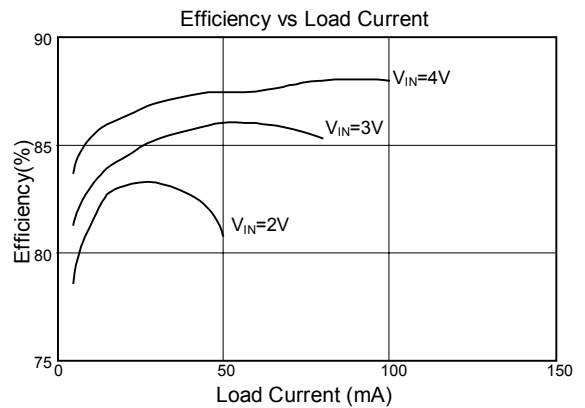
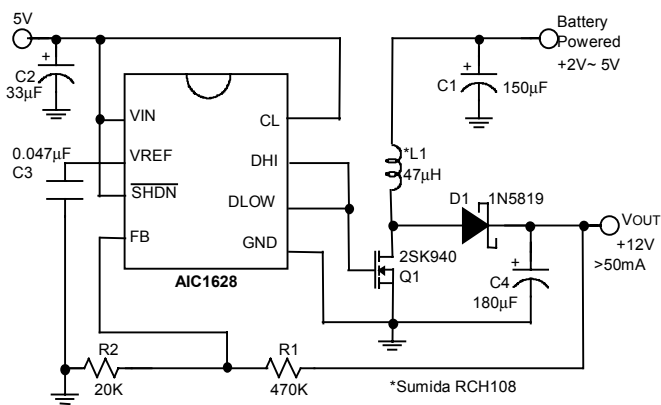


Fig. 2 2-cells to +12V Flash memory programmer

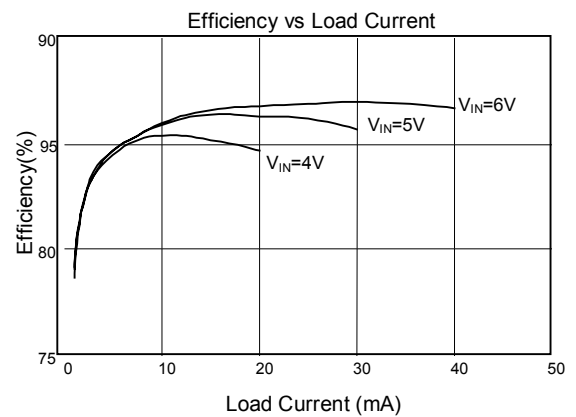
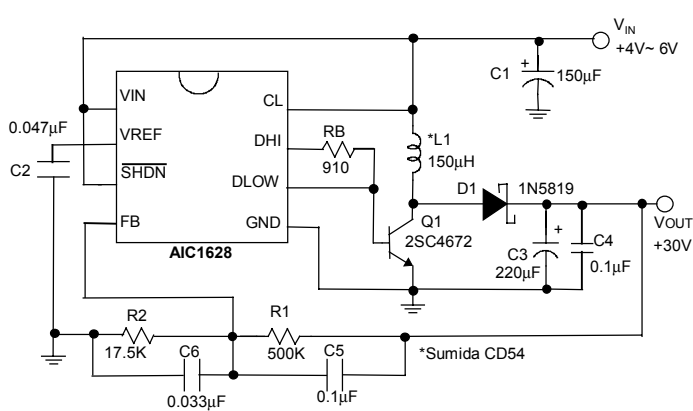


Fig. 3 4-cells to +30V power supply

APPLICATION EXAMPLES (CONTINUED)

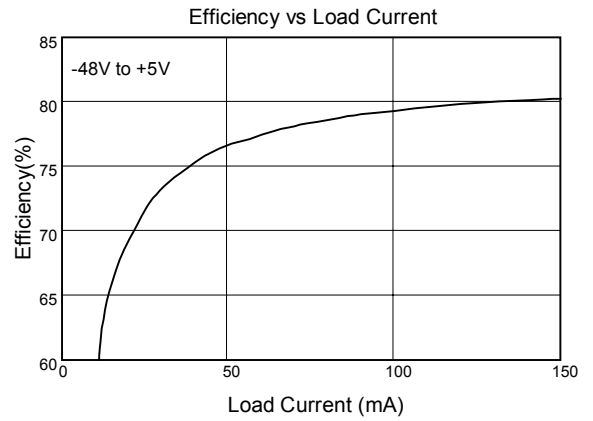
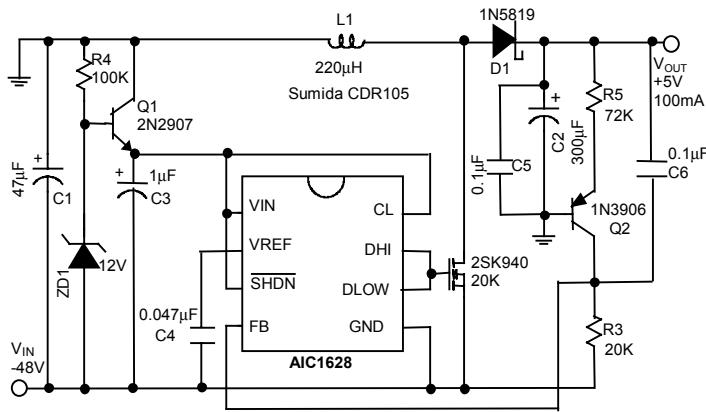


Fig. 4 Telecom +5V supply

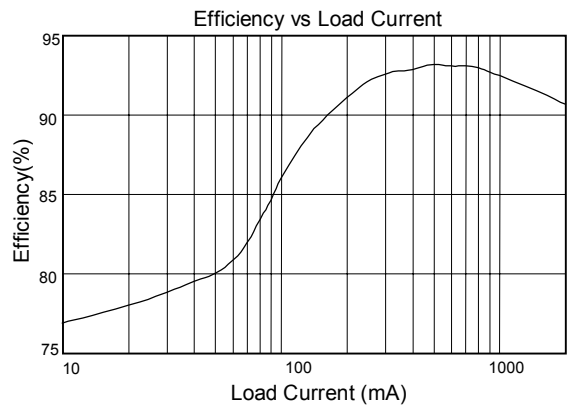
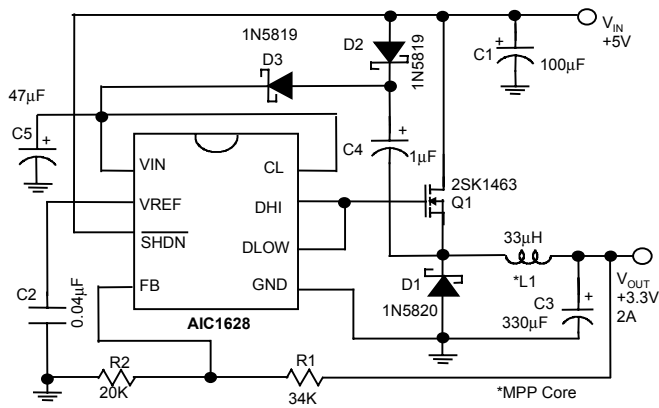
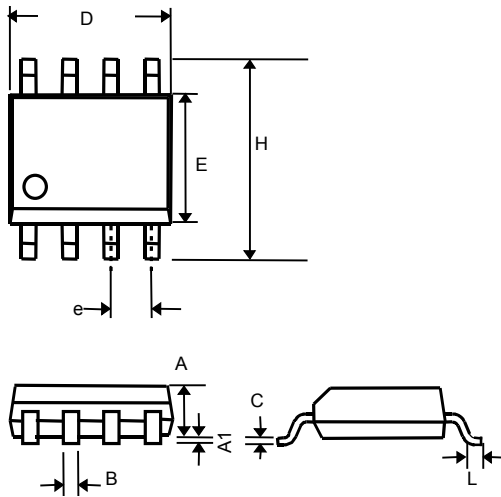
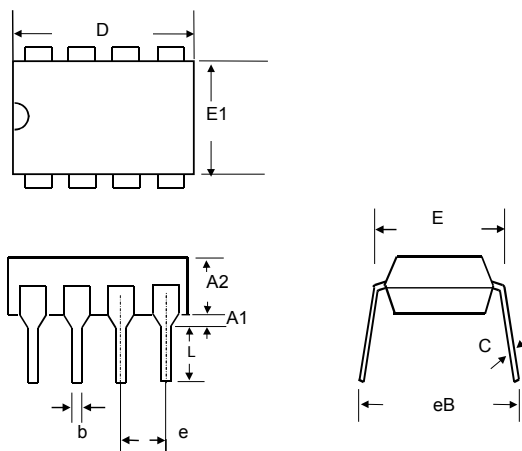


Fig. 5 5V to 3.3V step-down converter

PHYSICAL DIMENSIONS
● 8 LEAD PLASTIC SO (unit: mm)


| SYMBOL | MIN | MAX |
|--------|-----------|------|
| A | 1.35 | 1.75 |
| A1 | 0.10 | 0.25 |
| B | 0.33 | 0.51 |
| C | 0.19 | 0.25 |
| D | 4.80 | 5.00 |
| E | 3.80 | 4.00 |
| e | 1.27(TYP) | |
| H | 5.80 | 6.20 |
| L | 0.40 | 1.27 |

● 8 LEAD PLASTIC DIP (unit: mm)


| SYMBOL | MIN | MAX |
|--------|------------|-------|
| A1 | 0.381 | — |
| A2 | 2.92 | 4.96 |
| b | 0.35 | 0.56 |
| C | 0.20 | 0.36 |
| D | 9.01 | 10.16 |
| E | 7.62 | 8.26 |
| E1 | 6.09 | 7.12 |
| e | 2.54 (TYP) | |
| eB | — | 10.92 |
| L | 2.92 | 3.81 |

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.